Product data sheet

1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Fast switching
- Low forward voltage drop
- · Low thermal resistance
- Soft recovery characteristic
- Reduces switching losses in associated MOSFET or IGBT
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Switched-Mode Power Supplies
- · Power factor correction diode
- Uninterrupted Power Supply
- · Motor drive and SMPS freewheeling diode

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	1200	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	16	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	-	165	А
Static charact	eristics			'	'	
V _F	forward voltage	I _F = 16 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.3	3	V
		I _F = 32 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.8	3.9	V
		I _F = 16 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.8	2.7	V
Dynamic char	acteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	40	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K — A
2	Α	anode		001aaa020
mb	mb	mounting base; connected to cathode	TO-247 (SOD142)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYR16W-1200	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	1200	V
V_{RWM}	crest working reverse voltage		-	1200	V
V_R	reverse voltage	DC	-	1200	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	16	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 98 °C; squarewave pulse	-	32	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	-	165	Α
T _{stg}	storage temperature		-55	150	°C
Tj	junction temperature		-	150	°C

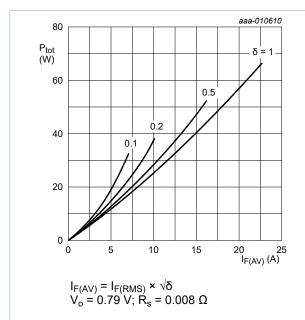
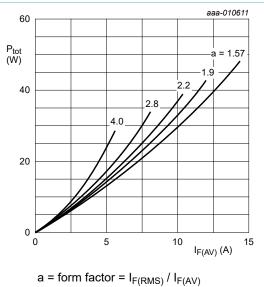


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}$ / $I_{F(AV)}$ V_o = 2.210 V; R_s = 0.032 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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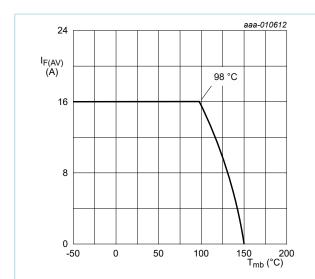


Fig. 3. Forward current as a function of mounting base temperature; maximum values

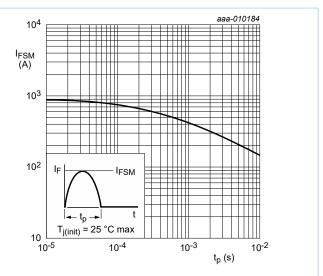


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

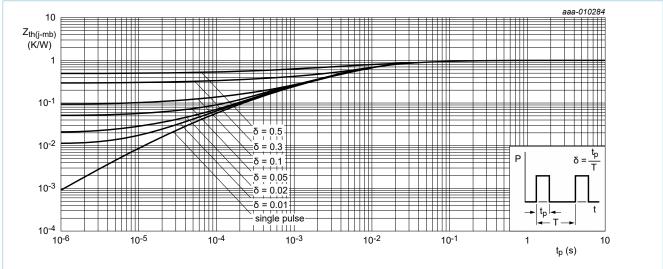


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

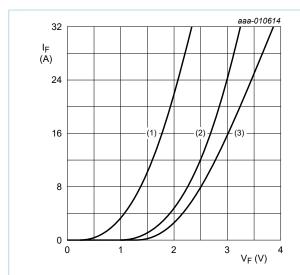
9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,		,	
V _F	forward voltage	I _F = 16 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.3	3	V
		I _F = 32 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.8	3.9	V
		I _F = 16 A; T _j = 125 °C; <u>Fig. 6</u>	-	1.8	2.7	V
R	reverse current	V _R = 1200 V; T _j = 25 °C	-	3	100	μA
		V _R = 1200 V; T _j = 125 °C	-	0.2	2	mA
Dynamic cl	naracteristics		1			
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	40	-	ns
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	90	-	ns
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	150	-	ns
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	105	-	ns
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	200	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	50	-	ns
I _{RM}	peak reverse recovery current	$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	11.2	-	Α
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	16	-	Α
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	11.2	-	Α
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	16.2	-	Α
Q _r	recovered charge	$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	520	-	nC
		$I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	1200	-	nC
		$I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	605	-	nC
		I _F = 16 A; V _R = 400 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u>	-	1600	-	nC

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 V_o = 2.210 V; R_s = 0.032 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values



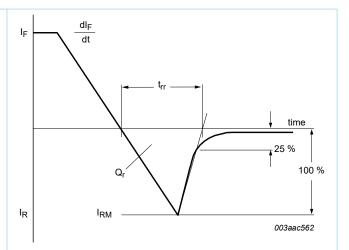
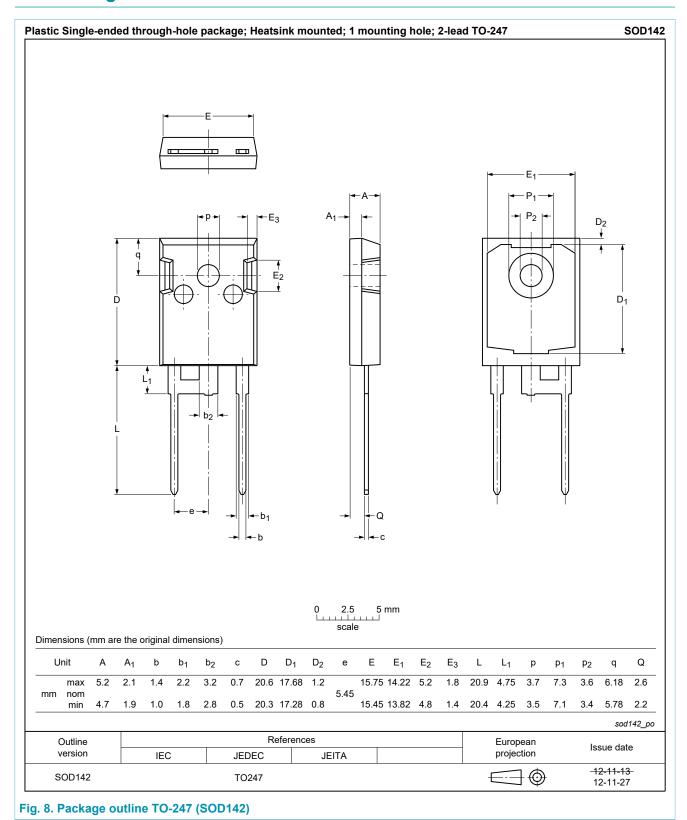


Fig. 7. Reverse recovery definitions; ramp recovery

10. Package outline



11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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